

Switch-mode Power Rectifier

Dual Schottky Rectifier

MBRB20200CTG, SBRB20200CTT4G

This device uses the Schottky Barrier technology with a platinum barrier metal. This state–of–the–art device is designed for use in high frequency switching power supplies and converters with up to 48 V outputs. They block up to 200 V and offer improved Schottky performance at frequencies from 250 kHz to 5.0 MHz.

Features

- 200 V Blocking Voltage
- Low Forward Voltage Drop
- Guardring for Stress Protection and High dv/dt Capability (10,000 V/μs)
- Dual Diode Construction Terminals 1 and 3 Must be Connected for Parallel Operation at Full Rating
- AEC-Q101 Qualified and PPAP Capable
- SBRB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb-Free*

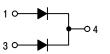
Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 1.7 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Rating:
 - ♦ Human Body Model = 3B
 - ♦ Machine Model = C

SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 200 V



D²PAK CASE 418B



MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

B20200 = Device Code

G = Pb-Free Package

AKA = Diode Polarity

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBRB20200CTG, SBRB20200CTT4G

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current (At Rated V_R , T_C = 134°C) Per Leg Per Device	I _{F(AV)}	10 20	А
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 20 kHz, T _C = +137°C) Per Leg	I _{FRM}	20	А
Nonrepetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	А
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	TJ	-65 to +150	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	2.0	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 1) $ \begin{pmatrix} I_F = 10 \text{ A}, T_C = 25^{\circ}\text{C}) \\ I_F = 10 \text{ A}, T_C = 125^{\circ}\text{C}) \\ I_F = 20 \text{ A}, T_C = 25^{\circ}\text{C}) \\ I_F = 20 \text{ A}, T_C = 125^{\circ}\text{C}) \end{pmatrix} $	V _F	0.9 0.8 1.0 0.9	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_C = 25^{\circ}C$) (Rated dc Voltage, $T_C = 125^{\circ}C$)	I _R	1.0 50	mA

DYNAMIC CHARACTERISTICS (Per Leg)

Capacitance	C _T		pF
$(V_R = -5.0 \text{ V}, T_C = 25^{\circ}\text{C}, \text{ Frequency} = 1.0 \text{ MHz})$		500	

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
SBRB20200CTT4G	D ² PAK (Pb-Free)	800 Units / Tape & Reel

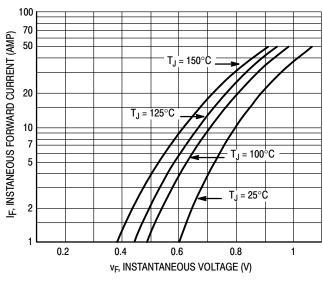
DISCONTINUED (Note 2)

MBRB20200CTG	D ² PAK (Pb-Free)	50 Units / Rail
MBRB20200CTT4G	D ² PAK (Pb-Free)	800 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{2.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

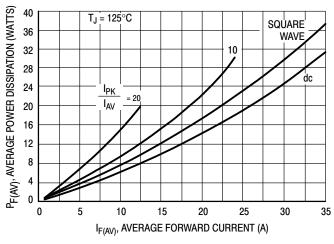
MBRB20200CTG, SBRB20200CTT4G



10,000 T_J = 150°C 1,000 T_J = 125°C IR, REVERSE CURRENT (μ.A) _{.I} = 100°C 0.1 $T_J = 25^{\circ}C$ 0.01 20 40 60 0 100 120 160 180 200 V_R, REVERSE CURRENT (V)

Figure 1. Typical Forward Voltage (Per Leg)

Figure 2. Typical Reverse Current (Per Leg)



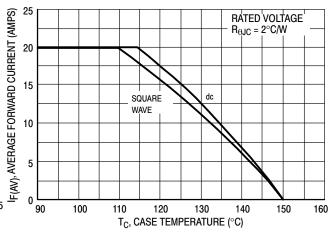
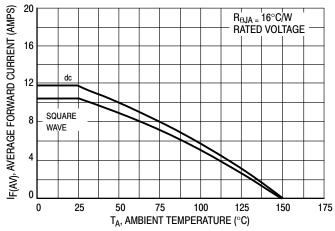


Figure 3. Forward Power Dissipation

Figure 4. Current Derating, Case





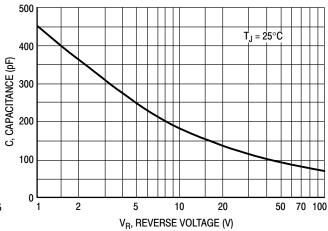


Figure 6. Typical Capacitance (Per Leg)

MECHANICAL CASE OUTLINE

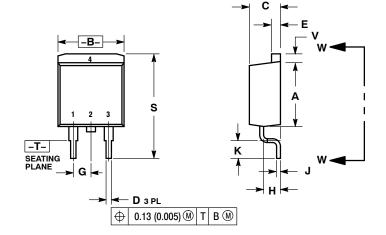




D²PAK 3 CASE 418B-04 **ISSUE L**

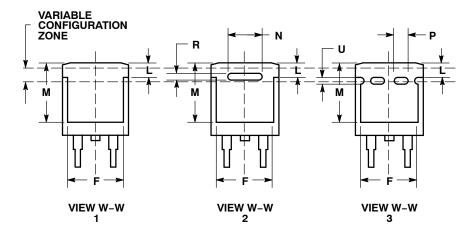
DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00	REF
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN

3. SOURCE 4. DRAIN

STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

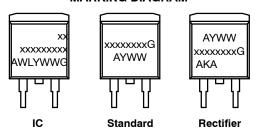
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DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

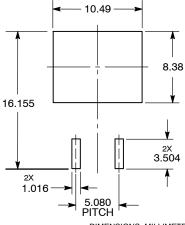
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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